

58 8/27/03

L Number	Hits	Search Text	DB	Time stamp
1	0	single adj lithography adj exposure	USPAT	2003/08/27 21:18
2	1047	438/758.ccls. or 438/759.ccls. or 438/778.ccls.	USPAT	2003/08/27 20:52
3	107	(438/758.ccls. or 438/759.ccls. or 438/778.ccls.) and lithography	USPAT	2003/08/27 20:52
4	2	(438/758.ccls. or 438/759.ccls. or 438/778.ccls.) and (lithography adj exposure)	USPAT	2003/08/27 20:53
5	223	lithography adj exposure	USPAT	2003/08/27 20:53
6	18	(lithography adj exposure) with resist	USPAT	2003/08/27 21:03
7	439	(novolak with resist) and lithography	USPAT	2003/08/27 21:04
8	33	(novolak with resist) and (lithography with single)	USPAT	2003/08/27 21:05
9	85	(novolak with resist) and (lithography with exposure)	USPAT	2003/08/27 21:24
11	557	(novolak with resist) and (lithography or photolithography) and exposure	USPAT	2003/08/27 21:24
12	132	(novolak with resist) and ((lithography or photolithography) with exposure)	USPAT	2003/08/27 21:42
13	82	(lithography or photolithography) with (one adj step)	USPAT	2003/08/27 21:55
14	459	(lithography or photolithography) and (single with exposure)	USPAT	2003/08/27 21:55
-	641	438/745.ccls.	USPAT	2003/08/27 17:44
-	1047	438/758.ccls. or 438/759.ccls. or 438/778.ccls.	USPAT	2003/08/27 20:52
-	600	(438/758.ccls. or 438/759.ccls. or 438/778.ccls.) and dielectric	USPAT	2003/08/27 17:51
-	57	(438/758.ccls. or 438/759.ccls. or 438/778.ccls.) and (dielectric and planar\$5 and etch\$3 and resist)	USPAT	2003/08/27 19:03
-	18	(438/758.ccls. or 438/759.ccls. or 438/778.ccls.) and ((dielectric with etch\$3) and (dielectric with planar\$5) and resist)	USPAT	2003/08/27 18:15
-	562	wafer and (dielectric with etch\$3) and (dielectric with planar\$5) and resist	USPAT	2003/08/27 20:52
-	1884	216/2.ccls. or 216/41.ccls. or 216/83.ccls.	USPAT	2003/08/27 19:17
-	702	(216/2.ccls. or 216/41.ccls. or 216/83.ccls.) and wafer	USPAT	2003/08/27 19:18
-	231	((216/2.ccls. or 216/41.ccls. or 216/83.ccls.) and wafer) and dielectric	USPAT	2003/08/27 20:39